



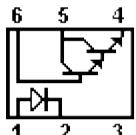
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H11B1, H11B2, H11B3 OPTICALLY COUPLED ISOLATORS

Circuit



Features

Dual-In-Line Package
High Sensitivity to Low Input Current
High Input-Output Isolation Guaranteed - 5300 Volts Peak
Various lead form options available

Description

The H11B1, H11B2, H11B3 are optically coupled isolators consisting of a Gallium Arsenide infrared emitter and a silicon photo darlington sensor. Switching can be accomplished while maintaining a high degree of isolation between driving and load circuits. They can be used to replace reed and mercury relays with advantages of long life, high speed switching and elimination of magnetic fields. Surface Mount Option Available.

All electrical parameters are 100% tested by manufacturing. Specifications are guaranteed to a cumulative 0.65% AQL.

Absolute Maximum Ratings: (Ta=25°C)

Storage Temperature:	-55°C to +150°C
Operating Temperature:	-55°C to +100°C
Lead Soldering:	260°C for 10s, 1.6mm from case
Isolation Surge Voltage:	5300Vac

Input LED

Forward DC Current:	60mA
Reverse DC Voltage:	3V
Power Dissipation:	150mW
Derate Linearly:	1.41mW/°C above 25°C

Output Detector

Collector-Emitter Voltage:	25V
Emitter-Base Voltage:	7V
Collector-Base Voltage:	30V
Collector Current - Continuous:	100V
Power Dissipation:	150mW
Derate Linearly:	1.76mW/°C above 25°C

Electro-optical Characteristics: (Ta=25°C)

INPUT	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V _F	Forward Voltage H11B1, H11B2	I _F =10mA		1.15	1.5	V
	Forward Voltage H11B3	I _F =50mA		1.34	1.5	V
I _R	Reverse Leakage Current	V _R =3.0V		10		µA
V _R	Capacitance	I _R =100µA , V=0V, f=1MHz	18			pF
OUTPUT	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
I _{CEO}	Collector-Emitter Dark Current	V _{CE} =10V	30			V
V _{(BR)CEO}	Collector-Emitter Breakdown V age	I _C =10mA				
V _{(BR)CBO}	Collector-Base Breakdown V age	I _C =100µA				
V _{(BR)ECO}	Emitter-Collector Breakdown V age	I _E =100µA				
h _{FE}	DC Current Gain	I _C =5mA, V _{CE} =5V				
C _{CE}	Collector-Emitter Capacitance	f=1MHz, V _{CE} =5V	5			V
C _{CB}	Collector-Base Capacitance	f=1MHz, V _{CB} =5V		100		nA
C _{EB}	Emitter-Base Capacitance	f=1MHz, V _{EB} =5V		10		pf
COUPLED	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
I _C	Output Collector Current H11B1	I _F =1mA, V _{CE} =5V	5			mA
	H11B2		2			mA
	H11B3		1			mA

$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage	$I_C=1\text{mA}$, $I_F=1\text{mA}$	0.7	1	Volts
T_{ON}	Turn-On Time	$I_F=5\text{mA}$, $V_{CC}=10\text{V}$, $R_L=100\text{ohm}$	3.5		μS
T_{OFF}	Turn-Off Time	$I_F=5\text{mA}$, $V_{CC}=10\text{V}$, $R_L=100\text{ohm}$	95		μS
t_R	Rise Time	$I_F=5\text{mA}$, $V_{CC}=10\text{V}$, $R_L=100\text{ohm}$	1		μS
t_F	Fall Time	$I_F=5\text{mA}$, $V_{CC}=10\text{V}$, $R_L=100\text{ohm}$	2		μS
V_{ISO}	Isolation Voltage	$f=60\text{Hz}$, $t=1\text{s}$ (note 1)	7500	5	Vac(pk)
R_{ISO}	Isolation Resistance	$V=500\text{V}$ (note 1)	1E11		ohm
C_{ISO}	Isolation Capacitance	$V=0\text{V}$, $f=1\text{Mhz}$ (note 1)	0.2	40	pF

1. For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.

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